## **UNIT 2. MOSFETS:'S THEORY**

- 1.1 What of the following statements on the MOSFET transistor is FALSE?
  - [A] It has an insulated gate made by a thin SiO<sub>2</sub> layer
  - [B]In the ohmic region, the transistor is equivalent to a resistance that increases if VGS increases 🔀
  - [C] In the saturation region, the current increases on a quadratic law with VGS /
  - [D] The PMOS transistor is slower than the NMOS.

 $\mu_p = \mu_n \Rightarrow (K_p)_p = (K_p)_n$   $K_p = \mu Cox$ 

LON= 2K EVOS-VT J V65# => RON V

IDS= K (VOS-V4)2

- 1.3. Indicate the FALSE statement among the following related to the enhancement MOSFET:
  - [A] It has an insulated gate.
  - [B] It is a unipolar and symmetrical device.
  - [C] In linear region, it works as a variable resistor dependent on the gate-source voltage VGS.
  - [D] In the saturation region, the current has a linear dependence on gate-source voltage VGS. 🔀

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